Silicon NPN Power Transistors 2SC2612

DESCRIPTION

·With TO-220 package

·High collector breakdown voltage

: V_{CEO}=400V(Min)

APPLICATIONS

·For high voltage ,high speed and high power switching applications

PINNING

PIN	DESCRIPTION
1	Base
2	Collector;connected to mounting base
3	Emitter

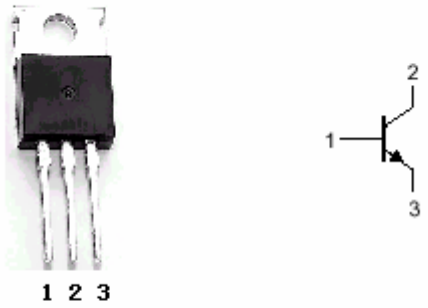

Fig.1 simplified outline (TO-220C) and symbol

Absolute maximum ratings(Ta=25□)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	500	V
V_{CEO}	Collector-emitter voltage	Open base	400	V
V_{EBO}	Emitter-base voltage	Open collector	7	V
I_C	Collector current		3	A
I_{CM}	Collector current-Peak		6	A
I_B	Base current		1.5	A
P_C	Collector power dissipation	T_C=25□	30	W
T_j	Junction temperature		150	□
T_{stg}	Storage temperature		-55~150	□

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CHARACTERISTICS

Tj=25□ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{CEO(SUS)}$	Collector-emitter sustaining voltage	I_C=0.2A ,R_{BE}=∞,L=100mH	400			V
$V_{(BR)EBO}$	Emitter-base breakdown voltage	I_E=10mA; I_C=0	7			V
V_{CEsat}	Collector-emitter saturation voltage	I_C=1.5A; I_B=0.3A			1.0	V
V_{BEsat}	Base-emitter saturation voltage	I_C=1.5A; I_B=0.3A			1.5	V
I_{CBO}	Collector cut-off current	V_{CB}=400V; I_E=0			100	μA
I_{CEO}	Collector cut-off current	V_{CE}=350V; R_{BE}=∞			100	μA
h_{FE-1}	DC current gain	I_C=1.5A ; V_{CE}=5V	15			
h_{FE-2}	DC current gain	I_C=3A ; V_{CE}=5V	7			

Switching times

t_{on}	Turn-on time	I_C=3.0A I_{B1}=- I_{B2}=0.6A V_{CC}≈150V			1.0	μs
t_{stg}	Storage time			1.2	2.5	μs
t_f	Fall time				1.0	μs

PACKAGE OUTLINE

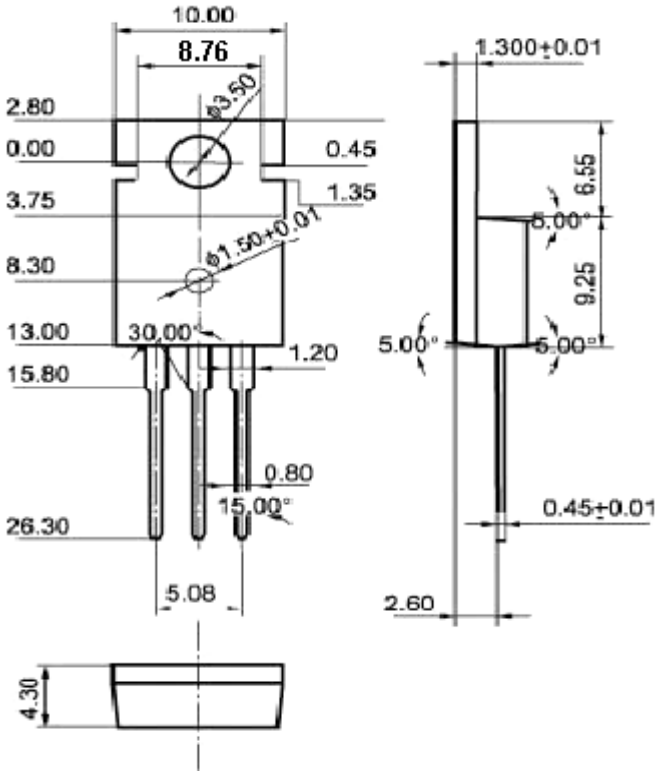

Fig.2 Outline dimensions(unindicated tolerance:±0.10 mm)

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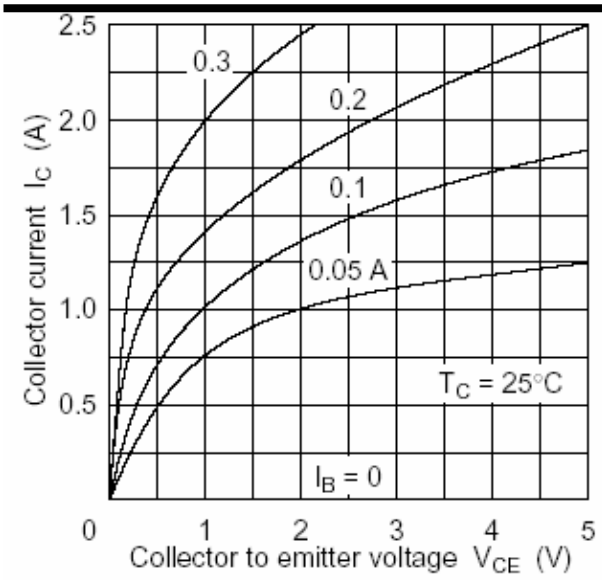

Fig.3 Static Characteristic

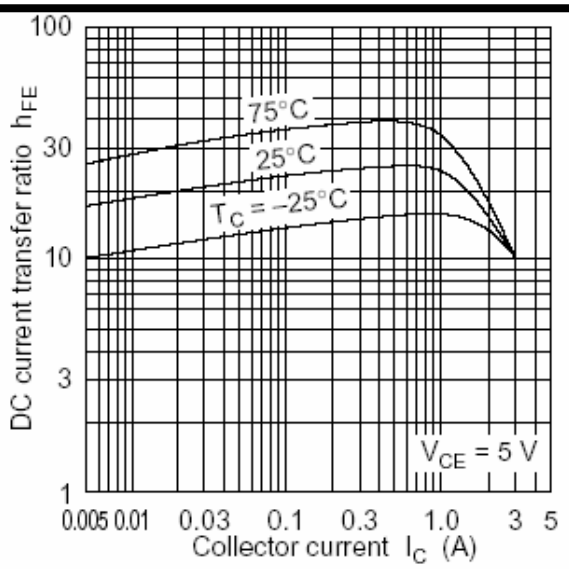

Fig.4 DC current Gain

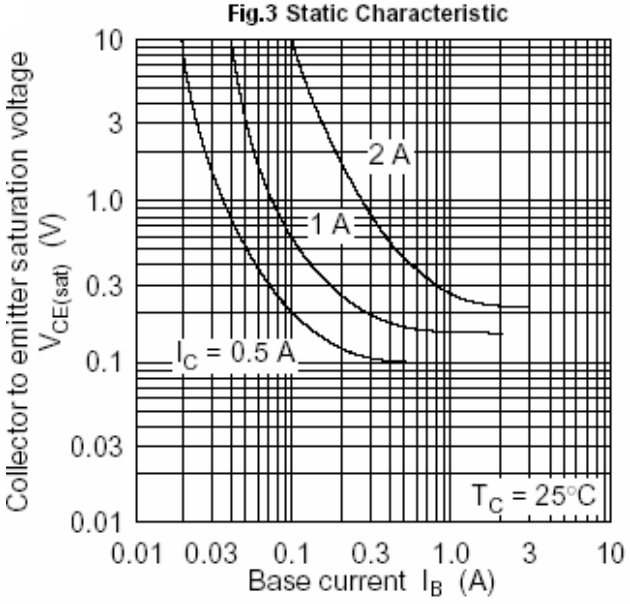

Fig.5 Collector-Emitter Saturation Voltage

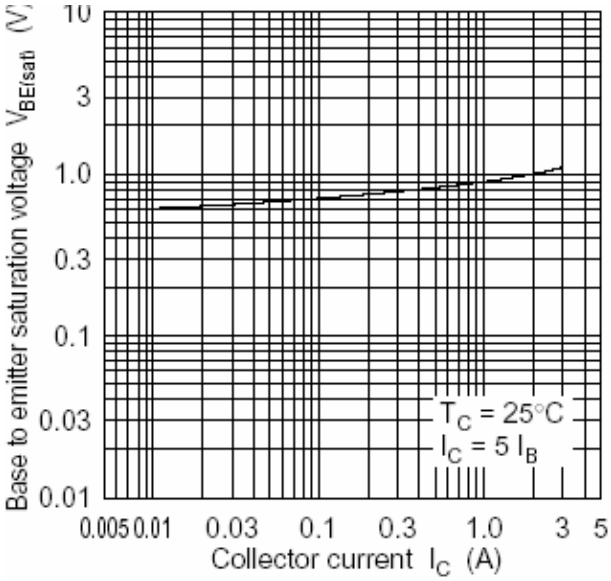

Fig.6 Base-Emitter Saturation Voltage

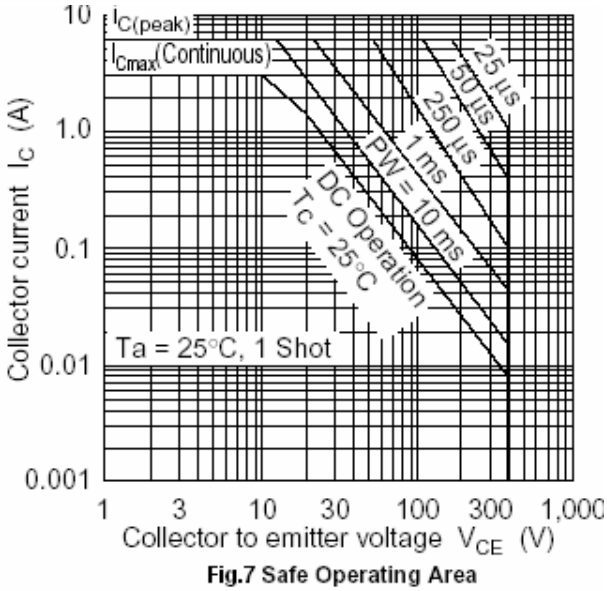

Fig.7 Safe Operating Area